1N4148ZP

Rev.D Nov.-2025

DATA SHEET

/ Descriptions

DFN1006-2L

Silicon Diode in a DFN1006-2L Plastic Package.

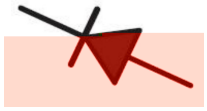
/ Features

Fast switching diodes, HF Product.

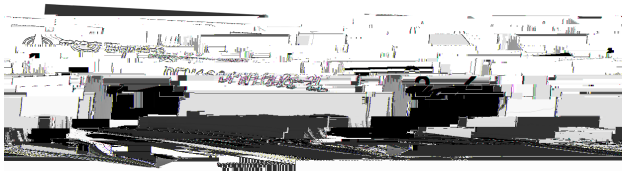
/ Applications

Small signal diode.

/ Equivalent Circuit



/ Pinning



PIN1:Anode PIN2:Cathode

/ Marking

Marking	HA2

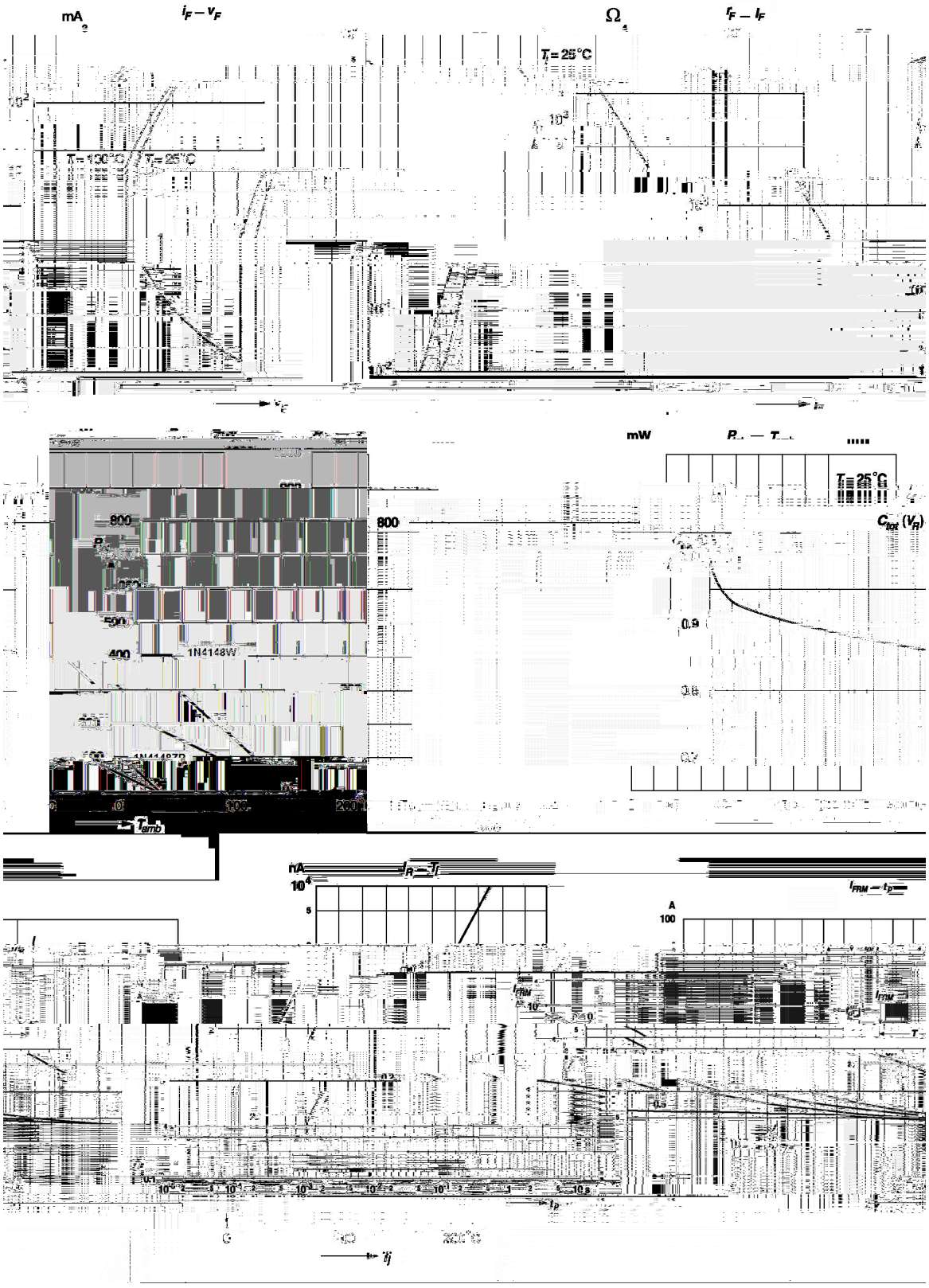
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_R	80	V
Peak Reverse Voltage	V_{RM}	100	V
Rectified Current (Average)	I_O	215	mA
Forward Continuous Current	I_{FM}	300	mA
repetitive peak forward current	I_{FRM} (tp≤0.5 μs;δ ≤ 0.25)	500	mA
Surge Forward Current	I_{FSM} t=1.0μs	4.0	A
	I_{FSM} t=1.0s	1.0	A
Power Dissipation	P_{tot}	250	mW
Operating and Storage Temperature Range	T_j ,T_{stg}	-55 +150	
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500	/W

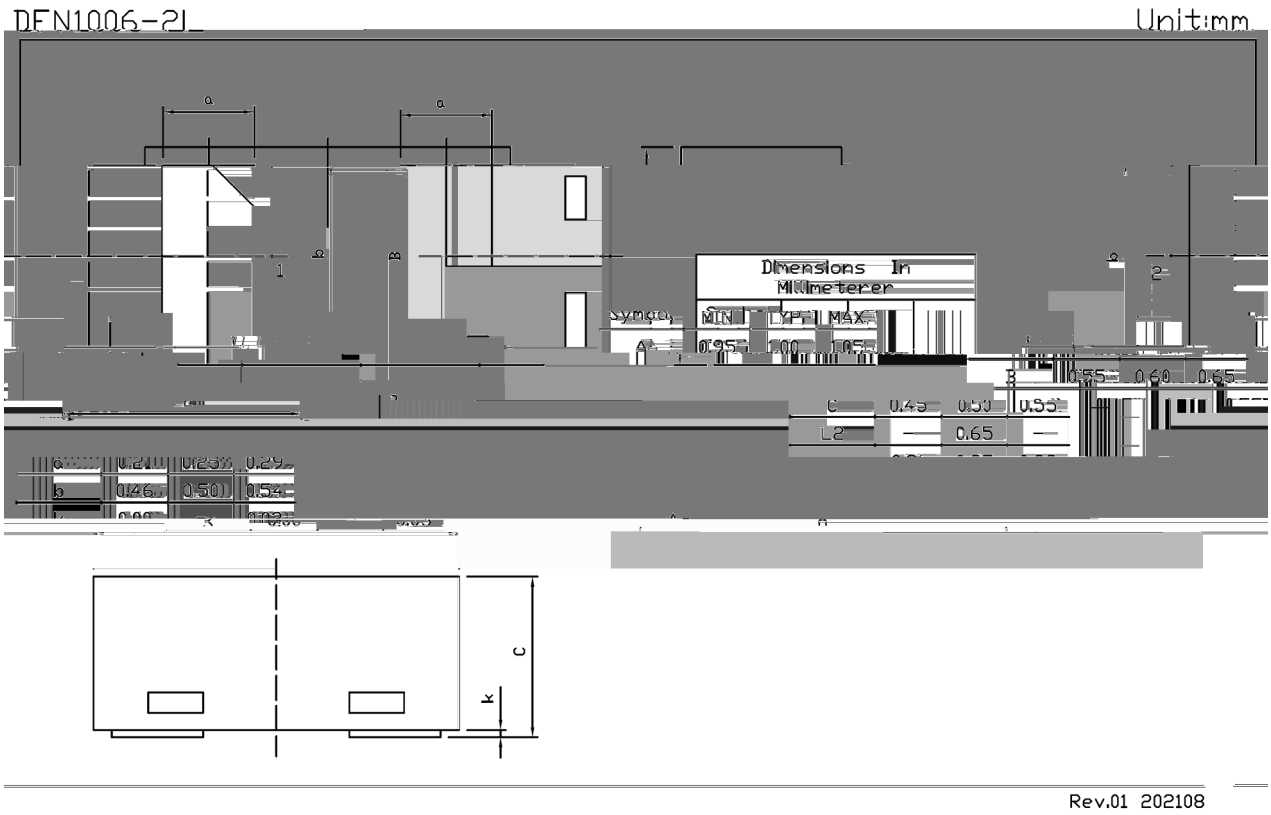
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F=1.0mA			715	mV
		I_F=10mA			855	mV
		I_F=50mA			1.0	V
		I_F=150mA			1.25	V
Instantaneous Reverse Current	I_R	V_R=20V			25	nA
		V_R=75V			5	μA
		V_R=20V T_j=150			50	μA
Capacitance	C_{tot}	V_F=V_R=0V			4	pF
Reverse Recovery Time	t_{rr}	I_F=10mA V_R=6.0V I_R=1mA R_L=100Ω			4	ns
Voltage Rise when Switching On tested	V_{fr}	tp=0.1μs fp=5to100kHz Time<30ns			2.5	V
Total Capacitance	C_T	V_R=0 f=1.0MHz			5.0	pF

/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



H

A2

Note:

H: Company Code

A2: Product Type Code